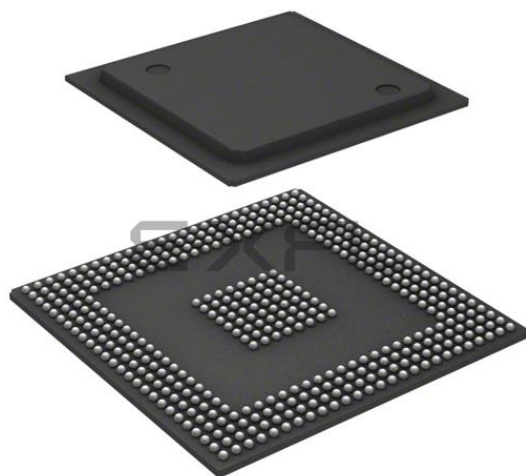




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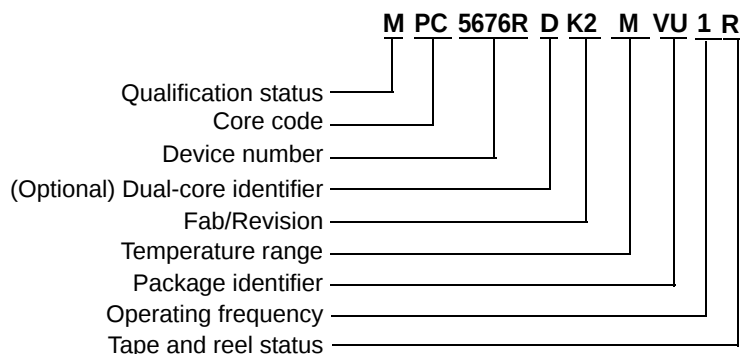
Details

Product Status	Active
Core Processor	e200z7
Core Size	32-Bit Dual-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, SCI, SPI
Peripherals	DMA, POR, PWM
Number of I/O	-
Program Memory Size	6MB (6M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 1.32V
Data Converters	A/D 64x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	416-BBGA
Supplier Device Package	416-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5676rdk3mvu1r

1 Ordering Information

1.1 Orderable Parts

Figure 1 and Table 1 describe and list the orderable part numbers for the MPC5676R.



Temperature Range
M = -40 °C to 125 °C

Package Identifier
VU = 416 TEPBGA
Pb-Free
VY = 516 TEPBGA
Pb-Free

Operating Frequency
1 = 2 x 180 MHz

Tape and Reel Status
R = Tape and reel
(blank) = Trays

Qualification Status
P = Pre qualification
M = Fully spec. qualified, general market flow
S = Fully spec. qualified, automotive flow

Note: Not all options are available on all devices. Refer to Table 1.

Figure 1. MPC5676R Orderable Part Number Description

Table 1. Orderable Part Numbers

NXP Part Number ¹	Package Description	Speed (MHz) ²		Operating Temperature ³	
		Nominal	Max ⁴ (f _{MAX})	Min (T _L)	Max (T _H)
SPC5676RDK2MVU1R	MPC5676R 416 package Lead-free (Pb-free)	180	184	-40 °C	125 °C
SPC5676RDK2MVY1R	MPC5676R 516 package Lead-free (Pb-free)	180	184	-40 °C	125 °C

¹ All packaged devices are PPC5676R, rather than MPC5676R or SPC5676R, until product qualifications are complete. The unpackaged device prefix is PCC, rather than SCC, until product qualification is complete. Not all configurations are available in the PPC parts.

² For the operating mode frequency of various blocks on the device, see Table 28.

³ The lowest ambient operating temperature is referenced by T_L; the highest ambient operating temperature is referenced by T_H.

⁴ Speed is the nominal maximum frequency. Max speed is the maximum speed allowed including frequency modulation (FM). 180 MHz parts allow for 180 MHz system clock + 2% FM.

3.3 Pin Muxing and Reset States

See Appendix A, Signal Properties and Muxing, for a listing and description of the pin functions and properties.

4 Electrical Characteristics

This section contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications for the MPC5676R.

The electrical specifications are preliminary and are from previous designs, design simulations, or initial evaluation. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle, however for production silicon these specifications will be met. Finalized specifications will be published after complete characterization and device qualifications have been completed.

4.1 Maximum Ratings

Table 2. Absolute Maximum Ratings¹

Spec	Characteristic	Symbol	Min	Max ²	Unit
1	1.2 V Core Supply Voltage ³	V_{DD}	-0.3	1.65 ⁴	V
2	SRAM Standby Voltage	V_{STBY}	-0.3	5.5 ^{5,6}	V
3	Clock Synthesizer Voltage	V_{DDSYN}	-0.3	4.5 ^{6,7}	V
4	I/O Supply Voltage (I/O buffers and predrivers)	V_{DD33}	-0.3	4.5 ^{6,7}	V
5	Analog Supply Voltage (reference to V_{SSA} ⁸)	V_{DDA} ⁹	-0.3	5.5 ^{5,6}	V
6	I/O Supply Voltage (fast I/O pads)	V_{DDE}	-0.3	4.5 ⁶	V
7	I/O Supply Voltage (medium I/O pads)	V_{DDEH}	-0.3	5.5 ^{5,6}	V
8	Voltage Regulator Input Supply Voltage	V_{DDREG}	-0.3	5.5 ^{5,6}	V
9	Analog Reference High Voltage (reference to V_{RL} ¹⁰)	V_{RH} ¹¹	-0.3	5.5 ^{5,6}	V
10	V_{SS} to V_{SSA} ⁸ Differential Voltage	$V_{SS} - V_{SSA}$	-0.1	0.1	V
11	V_{REF} Differential Voltage	$V_{RH} - V_{RL}$	-0.3	5.5 ^{5,6}	V
12	V_{RL} to V_{SSA} Differential Voltage	$V_{RL} - V_{SSA}$	-0.3	0.3	V
13	V_{DD33} to V_{DDSYN} Differential Voltage	$V_{DD33} - V_{DDSYN}$	-0.1	0.1	V
14	V_{SSSYN} to V_{SS} Differential Voltage	$V_{SSSYN} - V_{SS}$	-0.1	0.1	V
15	Maximum Digital Input Current ¹² (per pin, applies to all digital pins)	I_{MAXD}	-3 ¹³	3 ¹³	mA
16	Maximum Analog Input Current ¹⁴ (per pin, applies to all analog pins)	I_{MAXA}	-3 ^{9,13}	3 ^{9,13}	mA

Table 2. Absolute Maximum Ratings¹ (continued)

Spec	Characteristic	Symbol	Min	Max ²	Unit
17	Maximum Operating Temperature Range ¹⁵ – Die Junction Temperature	T _J	–40.0	150.0	°C
18	Storage Temperature Range	T _{stg}	–55.0	150.0	°C
19	Maximum Solder Temperature ¹⁶ Pb-free package SnPb package	T _{sdr}	— —	260.0 245.0	°C
20	Moisture Sensitivity Level ¹⁷	MSL	—	3	—

¹ Functional operating conditions are given in the DC electrical specifications. Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the listed maxima may affect device reliability or cause permanent damage to the device.

² Absolute maximum voltages are currently maximum burn-in voltages. Absolute maximum specifications for device stress have not yet been determined.

³ 1.2 V ±10% for proper operation. This parameter is specified at a maximum junction temperature of 150 °C.

⁴ 2.0 V for 10 hours cumulative time, 1.2 V +10% for time remaining.

⁵ 6.4 V for 10 hours cumulative time, 5.0 V +10% for time remaining.

⁶ Voltage overshoots during a high-to-low or low-to-high transition must not exceed 10 seconds per instance.

⁷ 4.5 V for 10 hours cumulative time, 3.3 V +10% for time remaining.

⁸ MPC5676R has two analog power supply pins on the pinout: VDDA_A and VDDA_B.

⁹ MPC5676R has two analog ground supply pins on the pinout: VSSA_A and VSSA_B.

¹⁰ MPC5676R has two analog low reference voltage pins on the pinout: VRL_A and VRL_B.

¹¹ MPC5676R has two analog high reference voltage pins on the pinout: VRH_A and VRH_B.

¹² Total injection current for all pins must not exceed 25 mA at maximum operating voltage.

¹³ Injection current of ±5 mA allowed for limited duration for analog (ADC) pads and digital 5 V pads. The maximum accumulated time at this current shall be 60 hours. This includes an assumption of a 5.25 V maximum analog or V_{DDEH} supply when under this stress condition.

¹⁴ Total injection current for all analog input pins must not exceed 15 mA.

¹⁵ Lifetime operation at these specification limits is not guaranteed.

¹⁶ Solder profile per CDF-AEC-Q100.

¹⁷ Moisture sensitivity per JEDEC test method A112.

4.2 Thermal Characteristics

Table 3. Thermal Characteristics, 416-pin TEPBGA Package¹

Characteristic	Symbol	Value	Unit
Junction to Ambient ^{2,3} Natural Convection (Single layer board)	R _{θJA}	24	°C/W
Junction to Ambient ^{2,4} Natural Convection (Four layer board 2s2p)	R _{θJA}	16	°C/W
Junction to Ambient (@200 ft./min., Single layer board)	R _{θJMA}	18	°C/W

Table 8. PMC Electrical Specifications

Spec	Name	Symbol	Condition	Min	Typ	Max	Unit
1c	Bandgap reference voltage / temperature dependence after power on reset	—	—	—	300	—	ppm/C
1d	Bandgap reference voltage / voltage dependence (V_{DDREG}) after power on reset	—	—	—	1500	—	
2	Nominal VRC regulated 1.2V output V_{DD}^1	$V_{DD12OUT}$	—	—	1.2	—	V
2a	VRC 1.2V output variation at reset (unloaded) ²	—	At POR	$V_{DD12OUT} - 8\%$	$V_{DD12OUT}$	$V_{DD12OUT} + 10\%$	
2b	VRC 1.2V output variation after reset (REGCTL load max. 20mA, V_{DD} load max. 1A)	—	After POR	$V_{DD12OUT} - 5\%$	$V_{DD12OUT}$	$V_{DD12OUT} + 10\%$	
2c	Trimming step V_{dd1p2}	$V_{STEPV12}$	—	—	10	—	mV
3	POR rising V_{DD} 1.2V	V_{PORC}	—	-	0.7	—	V
3a	POR V_{DD} 1.2V variation	—	—	$V_{PORC} - 30\%$	V_{PORC}	$V_{PORC} + 30\%$	
3b	POR 1.2V hysteresis	—	—	—	75	—	mV
4	Nominal rising LVD 1.2V ³	V_{LVD12}	—	—	1.100	—	V
4a	LVD 1.2V variation before band gap trim ⁴	—	At POR	$V_{LVD12} - 6\%$	V_{LVD12}	$V_{LVD12} + 6\%$	
4b	LVD 1.2V variation after band gap trim ⁴	—	After POR	$V_{LVD12} - 3\%$	V_{LVD12}	$V_{LVD12} + 3\%$	
4c	LVD 1.2V Hysteresis	—	—	15	20	25	mV
4d	Trimming step LVD 1.2V	$V_{LVDSTEP12}$	—	—	10	—	mV
5	VRC 1.2V max DC output current	I_{REGCTL}	—	—	—	20	mA
6	Voltage regulator 1.2V current consumption V_{DDREG}	—	—	—	3	—	mA
7	Nominal Vreg 3.3V output ⁵	$V_{DD33OUT}$	—	—	3.3	—	V
7a	Vreg 3.3V output variation at reset (unloaded) ⁶	—	At POR	$V_{DD33OUT} - 6\%$	$V_{DD33OUT}$	$V_{DD33OUT} + 10\%$	
7b	Vreg 3.3V output variation after reset (max. load 60mA)	—	After POR	$V_{DD33OUT} - 5\%$	$V_{DD33OUT}$	$V_{DD33OUT} + 10\%$	
7c	Trimming step V_{DDSYN}	$V_{STEPV33}$	—	—	30	—	mV
8	Nominal rising LVD 3.3V ⁷	V_{LVD33}	—	—	2.950	—	V
8a	LVD 3.3V variation before band gap trim ⁶	—	At POR	$V_{LVD33} - 5\%$	V_{LVD33}	$V_{LVD33} + 5\%$	
8b	LVD 3.3V variation after bad gap trim ⁶	—	After POR	$V_{LVD33} - 3\%$	V_{LVD33}	$V_{LVD33} + 3\%$	

Table 8. PMC Electrical Specifications

Spec	Name	Symbol	Condition	Min	Typ	Max	Unit
8c	LVD 3.3V Hysteresis	—	—	—	30	—	mV
8d	Trimming step LVD 3.3V	V _{LVDSTEP33}	—	—	30	—	mV
9	Vreg 3.3V minimum peak DC output current supplied by regulator without causing V _{LVD33} ⁸	I _{DD33}	—	60	—	—	mA
10	Voltage regulator 3.3V current consumption VDDREG ⁹	—	—	—	2	—	mA
11	POR rising on VDDREG	V _{PORREG}	—	—	2.00	—	V
11a	POR VDDREG variation	—	—	V _{PORREG} – 30%	V _{PORREG}	V _{PORREG} + 30%	
11b	POR VDDREG hysteresis	—	—	—	250	—	mV
12	Nominal rising LVD VDDREG	V _{LVDREG}	LDO3V / LDO5V mode	—	2.950	—	V
12a	LVD VDDREG variation at reset ¹⁰	—	At POR	V _{LVDREG} – 5%	V _{LVDREG}	V _{LVDREG} + 5%	
12b	LVD VDDREG variation after reset ¹⁰	—	After POR	V _{LVDREG} – 3%	V _{LVDREG}	V _{LVDREG} + 3%	
12c	LVD VDDREG Hysteresis	—	LDO3V / LDO5V mode	—	30	—	mV
12d	Trimming step LVD VDDREG	V _{LVDSTEPREG}	LDO3V / LDO5V mode	—	30	—	mV
13	Nominal rising LVD VDDREG	V _{LVDREG}	SMPS5V mode	—	4.360	—	V
13a	LVD VDDREG variation at reset ¹⁰	—	At POR	V _{LVDREG} – 5%	V _{LVDREG}	V _{LVDREG} + 5%	
13b	LVD VDDREG variation after reset ¹⁰	—	After POR	V _{LVDREG} – 3%	V _{LVDREG}	V _{LVDREG} + 3%	
14	SMPS regulator output resistance ¹¹	—	—	—	15	25	Ohm
15	SMPS regulator clock frequency	—	After POR	1.0	1.5	—	MHz
16	SMPS regulator overshoot at start-up ¹²	—	GBD/GBC ¹³	—	1.32	1.4	V
17	SMPS maximum output current, as required by SoC ¹⁴	—	—	—	1.0	—	A
18	Voltage variation on current step (20% to 80% of maximum current with 4 usec constant time) ¹⁴	—	GBD/GBC ¹³	—	—	0.1	V



Figure 6. VRC 1.2V buck SMPS LDO configuration with external MOS - Schottky diode

Table 9. VRC LDO recommended external devices

Part Name	Part Type	Nominal	Description
NJD2873	NPN		ON Semiconductor TM
Beta (Bf)			From 60 to 550
Vbe			From 0.4 V to 1.0 V
Vce			From 0.2 V to 0.6 V depends on package / power
	Capacitor	6 x 4.7 uF - 20 V	Ceramic low ESR—One for each VDD pin
	Capacitor	6 x 0.1 uF - 20 V	Ceramic —One capacitor for each VDD pin
	Capacitor	20 uF	Supply decoupling cap (close to bipolar collector)
	Capacitor	2.2 uF	Snubber cap, required with NJD2873 (on bipolar base)
	Resistor	12 Ω	Optional ESR for snubber cap

Table 15. V_{DD33} Pad Average DC Current¹

Spec	Pad Type	Symbol	Frequency (MHz)	Load ² (pF)	V_{DD33} (V)	V_{DDE} (V)	Drive/Slew Rate Select	Current (mA)
1	Medium	I_{33_MH}	—	—	3.6	5.5	—	0.0007
2	Fast	I_{33_FC}	66	10	3.6	3.6	00	0.92
3			66	20	3.6	3.6	01	1.14
4			66	30	3.6	3.6	10	1.50
5			66	50	3.6	3.6	11	2.19
6			66	10	3.6	1.98	00	0.70
7			66	20	3.6	1.98	01	0.90
8			66	30	3.6	1.98	10	1.08
9			66	50	3.6	1.98	11	1.52
10	Fast w/ Slew Control	I_{33_FSR}	66	50	3.6	3.6	11	0.74
11			50	50	3.6	3.6	10	0.52
12			33.33	50	3.6	3.6	01	0.36
13			20	50	3.6	3.6	00	0.19
14			20	200	3.6	3.6	00	0.19

¹ These are average I_{DD33} for worst case PVT from simulation. Currents apply to output pins only for the fast pads and to input pins only for the medium pads.

² All loads are lumped.

4.7.3 LVDS Pad Specifications

LVDS pads are implemented to support the MSC (Microsecond Channel) protocol, which is an enhanced feature of the DSPI module.

Table 16. DSPI LVDS Pad Specification^{1, 2}
($V_{DD33} = 3.0\text{ V to }3.6\text{ V}$, $V_{DDEH} = 4.75\text{ V to }5.25\text{ V}$, $T_A = T_L\text{ to }T_H$)

Spec	Characteristic	Symbol	Min	Typical	Max	Unit
Data Rate						
1	Data Frequency	$f_{LVDSCLK}$	—	—	40	MHz
Driver Specs						
2	Differential Output Voltage SRC=0b00 or 0b11 SRC=0b01 SRC=0b10	V_{OD}	215 170 260	—	400 320 480	mV
3	Common Mode Voltage (LVDS), VOS	V_{OS}	1.075	1.2	1.325	V
4	Rise/Fall Time	t_R or t_F	—	—	2.5	ns
5	Delay, Z to Normal (High/Low)	t_{DZ}	—	—	100	ns

Table 18. Oscillator Electrical Specifications¹ (continued)
 $(V_{DDSYN} = 3.0 \text{ V to } 3.6 \text{ V}, V_{SS} = V_{SSSYN} = 0 \text{ V}, T_A = T_L \text{ to } T_H)$

Spec	Characteristic	Symbol	Min	Max	Unit
7	Total On-chip stray capacitance on EXTAL	C_{S_EXTAL}	—	1.5	pF
8	Crystal manufacturer's recommended capacitive load	C_L	See crystal spec	See crystal spec	pF
9	Discrete load capacitance to be connected to EXTAL	C_{L_EXTAL}	—	$(2 \times C_L - C_{S_EXTAL} - C_{PCB_EXTAL})$	pF
10	Discrete load capacitance to be connected to XTAL	C_{L_XTAL}	—	$(2 \times C_L - C_{S_XTAL} - C_{PCB_XTAL})$	pF

¹ All values given are initial design targets and subject to change.

² This parameter is meant for those who do not use quartz crystals or resonators, but instead use CAN oscillators in crystal mode. In that case, $V_{extal} - V_{xtal} \geq 400 \text{ mV}$ criterion has to be met for oscillator's comparator to produce output clock.

³ I_{xtal} is the oscillator bias current out of the XTAL pin with both EXTAL and XTAL pins grounded.

⁴ C_{PCB_EXTAL} and C_{PCB_XTAL} are the measured PCB stray capacitances on EXTAL and XTAL, respectively.

4.9 eQADC Electrical Characteristics

Table 19. eQADC Conversion Specifications (Operating)

Spec	Characteristic	Symbol	Min	Max	Unit
1	ADC Clock (ADCLK) Frequency	f_{ADCLK}	2	16	MHz
2	Conversion Cycles	CC	2 + 13	128 + 14	ADCLK cycles
3	Stop Mode Recovery Time ¹	T_{SR}	10	—	μs
4	Resolution ²	—	1.25	—	mV
5	INL: 8 MHz ADC Clock ³	INL8	-4^4	4^4	LSB ⁵
6	INL: 16 MHz ADC Clock ³	INL16	-8^4	8^4	LSB
7	DNL: 8 MHz ADC Clock ³	DNL8	-3^4	3^4	LSB
8	DNL: 16 MHz ADC Clock ³	DNL16	-3^4	3^4	LSB
9	Offset Error without Calibration	OFFNC	0^4	100^4	LSB
10	Offset Error with Calibration	OFFWC	-4^4	4^4	LSB
11	Full Scale Gain Error without Calibration	GAINNC	-120^4	0^4	LSB
12	Full Scale Gain Error with Calibration	GAINWC	$-4^{4,6}$	$4^{4,6}$	LSB
13	Disruptive Input Injection Current ^{7, 8, 9, 10}	I_{INJ}	-1	1	mA
14	Incremental Error due to injection current ^{11, 12}	E_{INJ}	—	$\pm 4^4$	Counts
15	TUE value at 8 MHz ^{13, 14} (with calibration)	TUE8	—	$\pm 4^{4,6}$	Counts

4.9.1 ADC Internal Resource Measurements

Table 20. Power Management Control (PMC) Specification

Spec	Characteristic	Symbol	Min	Typical	Max	Unit
PMC Normal Mode						
1	Bandgap 0.62 V ADC0 channel 145	V_{ADC145}	0.59	0.62	0.65	V
2	Bandgap 1.2 V ADC0 channel 146	V_{ADC146}	1.10	1.22	1.34	V
3	Vreg1p2 Feedback ADC0 channel 147	V_{ADC147}	$V_{DD}/2.147$	$V_{DD} / 2.045$	$V_{DD}/1.943$	V
4	LVD 1.2 V ADC0 channel 180	V_{ADC180}	$V_{DD}/1.863$	$V_{DD} / 1.774$	$V_{DD}/1.685$	V
5	Vreg3p3 Feedback ADC0 channel 181	V_{ADC181}	Vreg3p3 / 5.733—	Vreg3p3 / 5.460	Vreg3p3 / 5.187	V
6	LVD 3.3 V ADC0 channel 182	V_{ADC182}	Vreg3p3 / 4.996	Vreg3p3 / 4.758	Vreg3p3 / 4.520	V
7	LVD 5.0 V ADC0 channel 183 — LDO mode — SMPS mode	V_{ADC183}	$V_{DDREG} / 4.996$ $V_{DDREG} / 7.384$	$V_{DDREG} / 4.758$ $V_{DDREG}/7.032$	$V_{DDREG} / 4.520$ $V_{DDREG} / 6.680$	V

Table 21. Standby RAM Regulator Electrical Specifications

Spec	Characteristic	Symbol	Min	Typ	Max	Unit
Normal Mode						
1	Standby Regulator Output ADC1 channel 194	V_{ADC194}	—	1.2	—	V
2	Standby Source Bias ADC1 channel 195	V_{ADC195}	150	—	360	mV

Table 22. ADC Band Gap Reference / LVI Electrical Specifications

Spec	Characteristic	Symbol	Min	Typ	Max	Unit
1	4.75 LVD (from V_{DDA}) ADC1 channel 196	V_{ADC196}	—	4.75	—	V
2	ADC Bandgap ADC0 channel 45 ADC1 channel 45	V_{ADC45}	—	1.220	—	V

Electrical Characteristics

- ¹ These are worst case values that are estimated from simulation and not tested. The values in the table are simulated at $V_{DD} = 1.08 \text{ V}$ to 1.32 V , $V_{DDE} = 3.0 \text{ V}$ to 3.6 V , $V_{DDEH} = 3.0 \text{ V}$ to 3.6 V , V_{DD33} and $V_{DDSYN} = 3.0 \text{ V}$ to 3.6 V , $T_A = T_L$ to T_H .
- ² This parameter is supplied for reference and is not guaranteed by design and not tested.
- ³ Delay and rise/fall are measured to 20% or 80% of the respective signal.
- ⁴ This parameter is guaranteed by characterization before qualification rather than 100% tested.
- ⁵ Out delay is shown in Figure 7. Add a maximum of one system clock to the output delay for delay with respect to system clock.

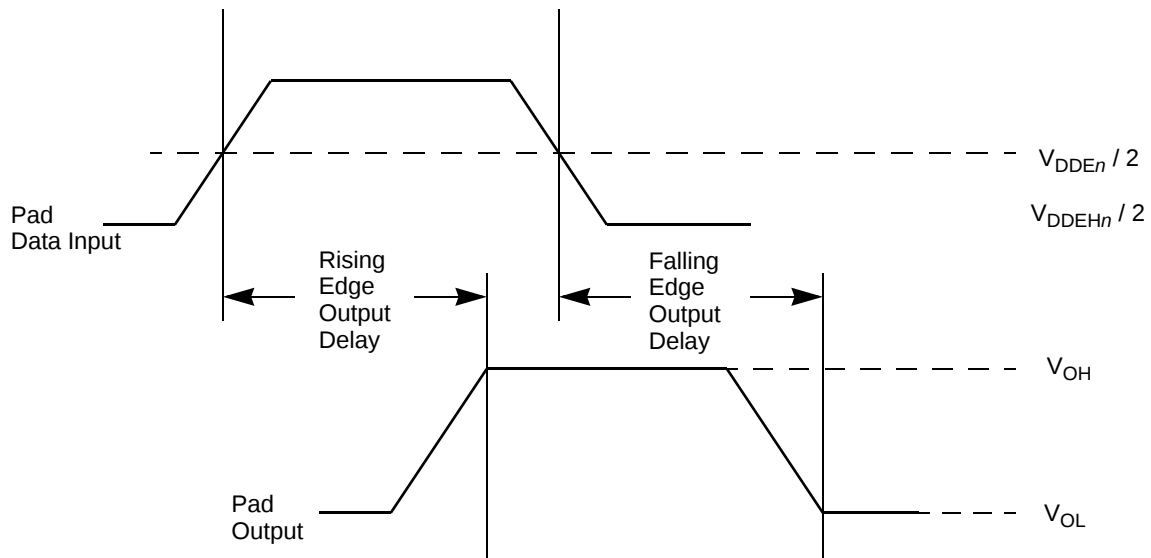


Figure 7. Pad Output Delay

4.12 AC Timing

4.12.1 Generic Timing Diagrams

The generic timing diagrams in Figure 8 and Figure 9 apply to all I/O pins with pad types F and MH. See Table 39 for the pad type for each pin.

Table 32. JTAG Pin AC Electrical Characteristics¹ (continued)

Spec	Characteristic	Symbol	Min	Max	Unit
12	TCK Falling Edge to Output Valid out of High Impedance	t_{BSDVZ}	—	50	ns
13	TCK Falling Edge to Output High Impedance	t_{BSDHZ}	—	50	ns
14	Boundary Scan Input Valid to TCK Rising Edge	t_{BSDST}	50	—	ns
15	TCK Rising Edge to Boundary Scan Input Invalid	t_{BSDHT}	50	—	ns

¹ JTAG timing specified at $V_{\text{DD}} = 1.08 \text{ V}$ to 1.32 V , $V_{\text{DDE}} = 3.0 \text{ V}$ to 3.6 V , V_{DD33} and $V_{\text{DDSYN}} = 3.0 \text{ V}$ to 3.6 V , $T_{\text{A}} = T_{\text{L}}$ to T_{H} , and $C_{\text{L}} = 30 \text{ pF}$ with $\text{DSC} = 0\text{b}10$, $\text{SRC} = 0\text{b}00$. These specifications apply to JTAG boundary scan only. See Table 33 for functional specifications.

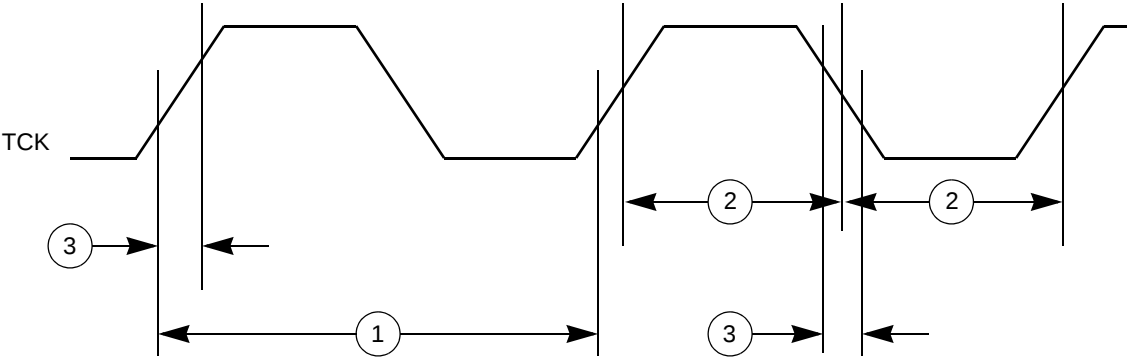


Figure 11. JTAG Test Clock Input Timing

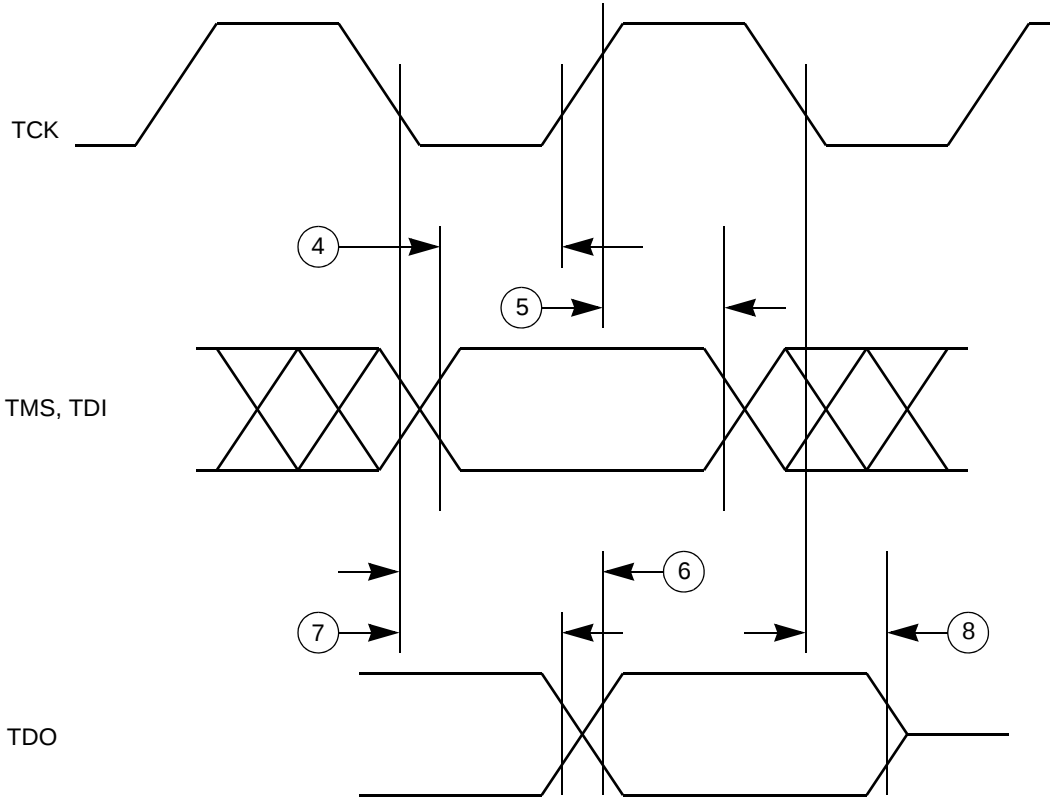


Figure 12. JTAG Test Access Port Timing

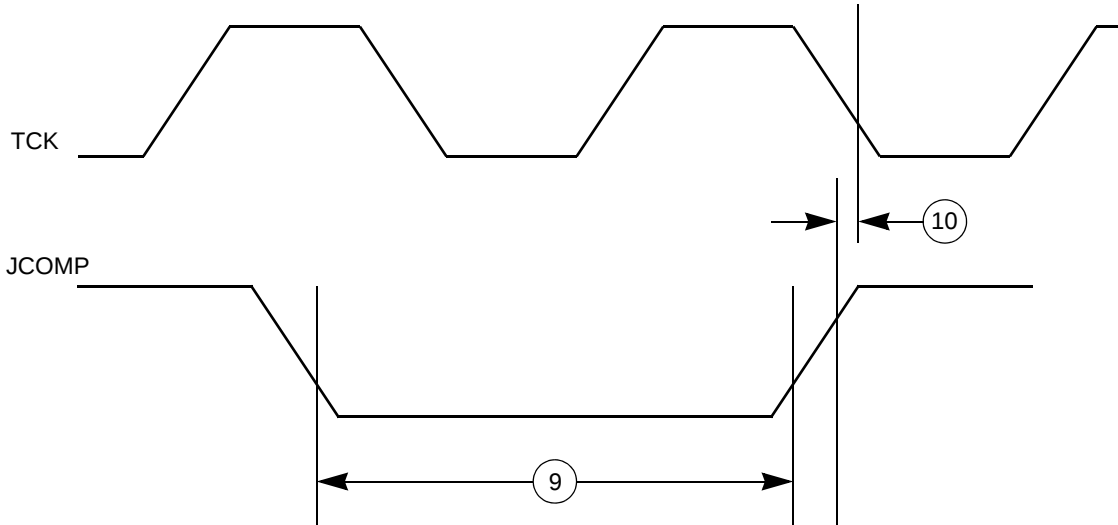


Figure 13. JTAG JCOMP Timing

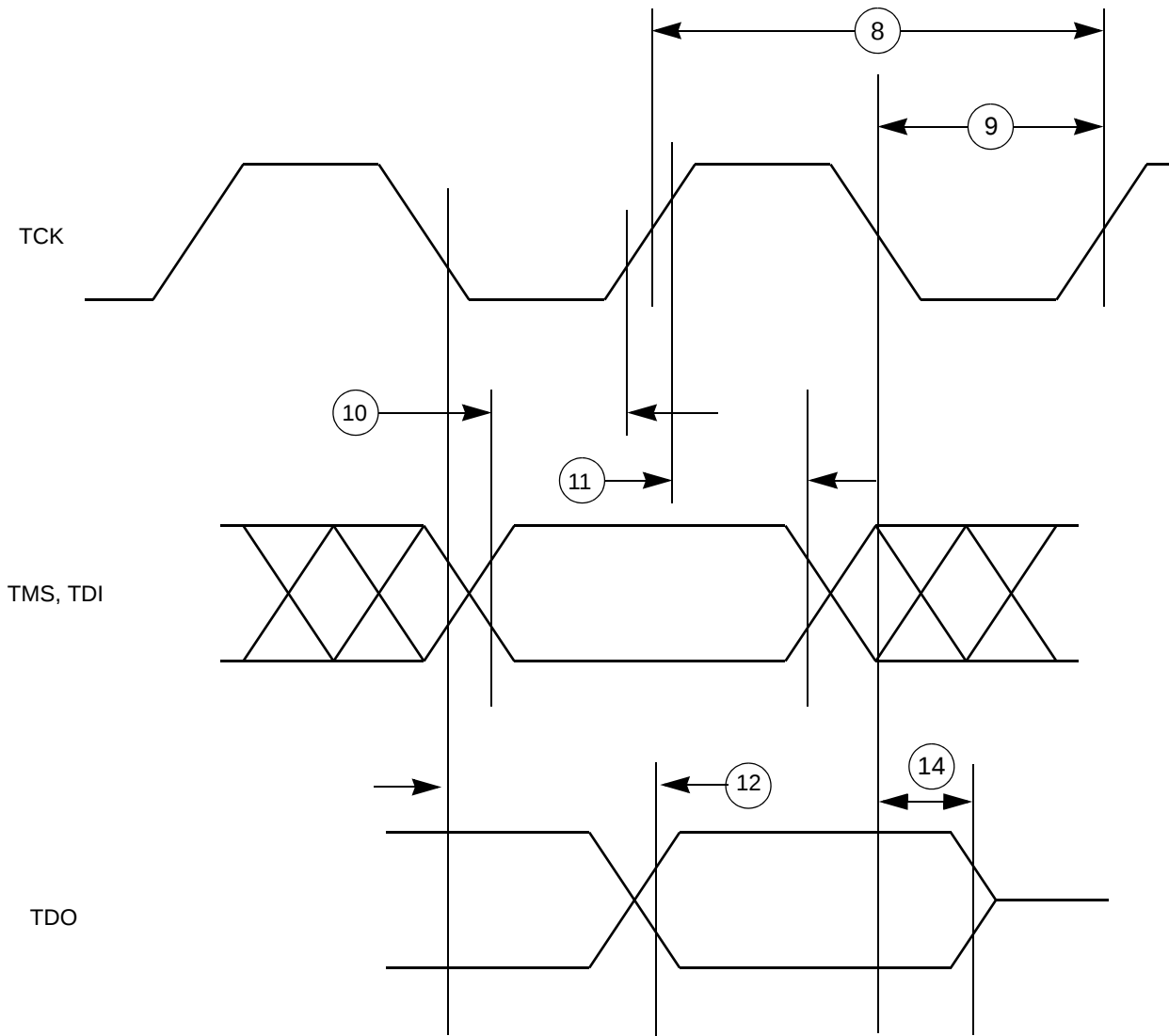


Figure 16. Nexus TCK, TDI, TMS, TDO Timing

4.12.5 External Bus Interface (EBI) Timing

Table 34. Bus Operation Timing ¹

Spec	Characteristic	Symbol	66 MHz (Ext. Bus Freq) ^{2 3}		Unit	Notes
			Min	Max		
1	D_CLKOUT Period	t _C	15.2	—	ns	Signals are measured at 50% V _{DDE} .

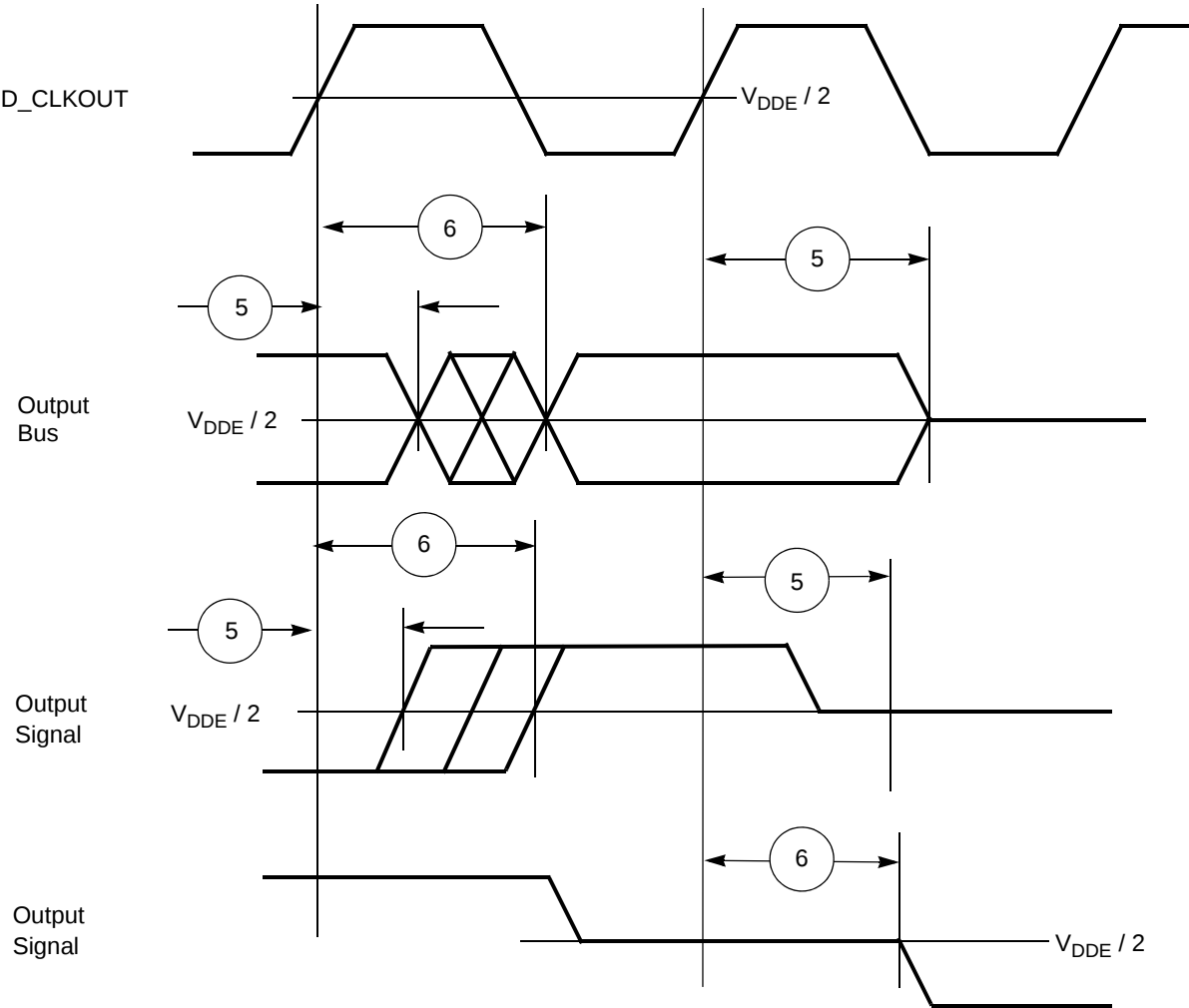


Figure 18. Synchronous Output Timing

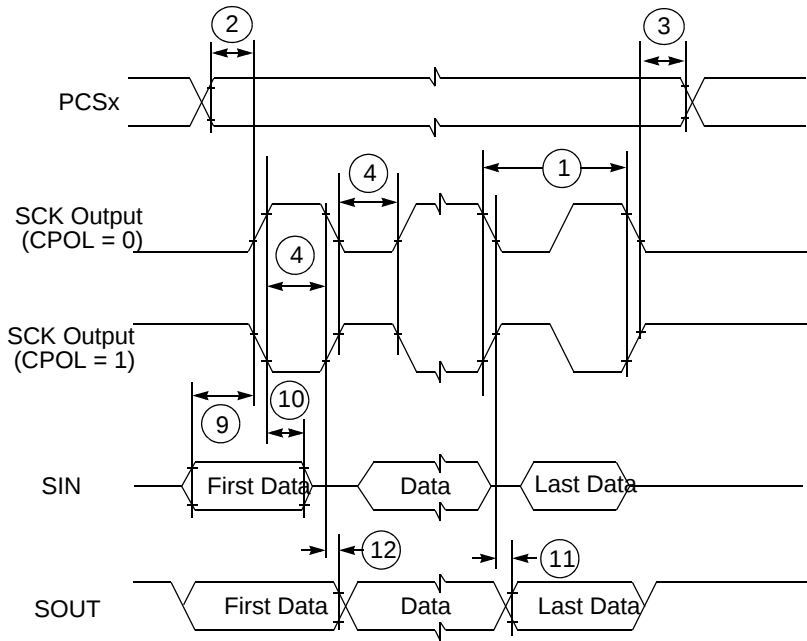


Figure 24. DSPI Classic SPI Timing — Master, CPHA = 0

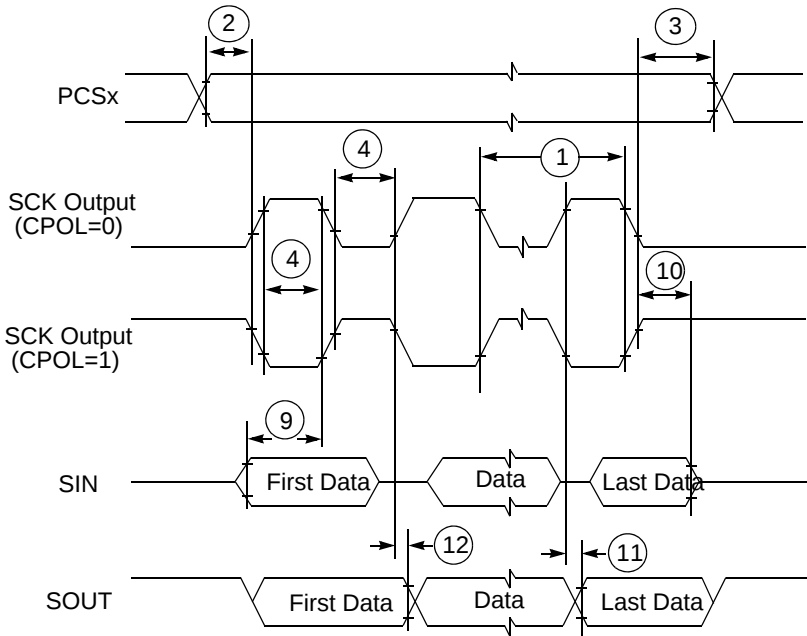


Figure 25. DSPI Classic SPI Timing — Master, CPHA = 1

5 Package Information

5.1 416-Pin Package

The package drawings of the 416-pin TEPBGA package are shown in Figure 33 and Figure 34.

Figure 33. 416 TEPBGA Package (1 of 2)

Figure 36. 516 TEPBGA Package (2 of 2)

Table 39. Signal Properties and Muxing Summary (continued)

GPIO/PCR ¹	Signal Name ²	P/A/G ³	Function ⁴	Function Summary	Direction	Pad Type ⁵	Voltage ⁶	State during RESET ⁷	State after RESET ⁸	Package Location	
										416	516
196	EMIOS17_ETPUB1_GPIO196	P	EMIOS17	eMIOS channel	I/O	MH	V _{DDEH4}	—/WKPCFG	—/WKPCFG	AE15	AB15
		A1	ETPUB1	eTPU B channel	O						
		A2	FR_DBG[2]	FlexRay debug	O						
		G	GPIO196	GPIO	I/O						
197	EMIOS18_ETPUB2_GPIO197	P	EMIOS18	eMIOS channel	I/O	MH	V _{DDEH4}	—/WKPCFG	—/WKPCFG	AC15	AD17
		A1	ETPUB2	eTPU B channel	O						
		A2	FR_DBG[1]	FlexRay debug	O						
		G	GPIO197	GPIO	I/O						
198	EMIOS19_ETPUB3_GPIO198	P	EMIOS19	eMIOS channel	I/O	MH	V _{DDEH4}	—/WKPCFG	—/WKPCFG	AD15	AB16
		A1	ETPUB3	eTPU B channel	O						
		A2	FR_DBG[0]	FlexRay debug	O						
		G	GPIO198	GPIO	I/O						
199	EMIOS20_ETPUB4_GPIO199	P	EMIOS20	eMIOS channel	I/O	MH	V _{DDEH4}	—/WKPCFG	—/WKPCFG	AF16	AF16
		A1	ETPUB4	eTPU B channel	O						
		A2	—	—	—						
		G	GPIO199	GPIO	I/O						
200	EMIOS21_ETPUB5_GPIO200	P	EMIOS21	eMIOS channel	I/O	MH	V _{DDEH4}	—/WKPCFG	—/WKPCFG	AE16	AE17
		A1	ETPUB5	eTPU B channel	O						
		A2	—	—	—						
		G	GPIO200	GPIO	I/O						
201	EMIOS22_ETPUB6_GPIO201	P	EMIOS22	eMIOS channel	I/O	MH	V _{DDEH4}	—/WKPCFG	—/WKPCFG	AC16	AC16
		A1	ETPUB6	eTPU B channel	O						
		A2	—	—	—						
		G	GPIO201	GPIO	I/O						

[illegible]

Table 39. Signal Properties and Muxing Summary (continued)

GPIO/PCR ¹	Signal Name ²	P/A/G ³	Function ⁴	Function Summary	Direction	Pad Type ⁵	Voltage ⁶	State during RESET ⁷	State after RESET ⁸	Package Location	
										416	516
82	MDO11_GPIO82	_12	MDO11 ¹⁴	Nexus message data out	O	F	V _{DDE2}	O/Low	—/Down	Y3	Y4
		A1	—	—	—						
		A2	—	—	—						
		G	GPIO82	GPIO	I/O						
231	MDO12_GPIO231	_12	MDO12 ¹⁴	Nexus message data out	O	F	V _{DDE2}	O/Low	—/Down	AA1	Y5
		A1	—	—	—						
		A2	—	—	—						
		G	GPIO231	GPIO	I/O						
232	MDO13_GPIO232	_12	MDO13 ¹⁴	Nexus message data out	O	F	V _{DDE2}	O/Low	—/Down	AA2	AA1
		A1	—	—	—						
		A2	—	—	—						
		G	GPIO232	GPIO	I/O						
233	MDO14_GPIO233	_12	MDO14 ¹⁴	Nexus message data out	O	F	V _{DDE2}	O/Low	—/Down	AA3	AA2
		A1	—	—	—						
		A2	—	—	—						
		G	GPIO233	GPIO	I/O						
234	MDO15_GPIO234	_12	MDO15 ¹⁴	Nexus message data out	O	F	V _{DDE2}	O/Low	—/Down	Y4	AA3
		A1	—	—	—						
		A2	—	—	—						
		G	GPIO234	GPIO	I/O						
224	MSEO0	_12	MSEO0 ¹⁴	Nexus message start/end out	O	F	V _{DDE2}	O/Low	MSEO/HI	U2	U6
225	MSEO1	_12	MSEO1 ¹⁴	Nexus message start/end out	O	F	V _{DDE2}	O/Low	MSEO/HI	T3	U5
226	RDY	_12	RDY	Nexus ready output	O	F	V _{DDE2}	O/Low	RDY/HI	R4	U3
—	TCK	_12	TCK	JTAG test clock input	I	F	V _{DDE2}	TCK/Down	TCK/Down	AB2	AB2
—	TDI	_12	TDI	JTAG test data input	I	F	V _{DDE2}	TDI/Up	TDI/Up	AC2	AC2
228	TDO	_12	TDO	JTAG test data output	O	F	V _{DDE2}	TDO/Up	TDO/Up	AB1	AB1
—	TMS	_12	TMS	JTAG test mode select input	I	F	V _{DDE2}	TMS/Up	TMS/Up	AB3	AB3